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## N 沟道 SuperFET® II MOSFET

**600 V, 22 A, 170 m**Ω

### 特性

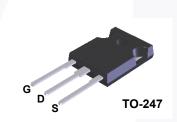
- 650 V @T<sub>J</sub> = 150°C
- 典型值 R<sub>DS(on)</sub> = 150 mΩ
- 超低栅极电荷 (典型值 Q<sub>q</sub> = 42 nC)
- 低有效输出电容 (典型值 C<sub>oss(eff.)</sub>=190 pF)
- 100% 经过雪崩测试
- 符合 RoHS 标准

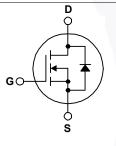
### 应用

- 通信 / 服务器电源
- 工业电源
- AC-DC 电源



SuperFET<sup>®</sup> II MOSFET 是 飞兆半导体 利用电荷平衡技术实现出 色的低导通电阻和更低栅极电荷性能的全新高压超级结 (SJ) MOSFET 系列产品。这项先进技术专用于最小化传导损耗,提供 卓越的开关性能,并能够承受极端 dv/dt 额定值和更高雪崩能 量。因此, SuperFET II MOSFET 适用于系统小型化和高效化的 各种各样的 AC-DC 功率转换的应用中。





### 绝对最大额定值 Tc=25°C除非另有说明。

符号			FCH170N60	単位		
V <sub>DSS</sub>	参数   漏极一源极电压			600	V	
V <sub>GSS</sub>		- DC		±20	- V	
	栅极一源极电压	- AC	±30			
ID		- 连续 (T <sub>C</sub> = 25°C)		22	А	
	漏极电流	- 连续 (T <sub>C</sub> = 100°C)		14	- A	
I <sub>DM</sub>	漏极电流	- 脉冲	(注1)	66	А	
E <sub>AS</sub>	单脉冲雪崩能量 (注 2)			525	mJ	
I <sub>AR</sub>	雪崩电流	(注1)	5	Α		
E <sub>AR</sub>	重复雪崩能量	(注1)	2.27	mJ		
dv/dt	MOSFET dv/dt (注3)			100	V/ns	
	二极管恢复 dv/dt 峰值			20		
P <sub>D</sub>	T+ #I	(T <sub>C</sub> = 25°C)		227	Ω	
	功耗	- 高于 25°C 的功耗系数		1.82	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	工作和存储温度范围			-55 至 +150	°C	
TL	用于焊接的最高引脚温度, 距离外壳 1/8",持续 5 秒			300	°C	

### 热性能

符号	参数	FCH170N60	单位	
R <sub>θJC</sub>	结至外壳热阻最大值	0.55	°C/W	
R <sub>θJA</sub>	结至环境热阻最大值	40	C/W	

FCH170N60 ---

2014年9月

器件标识 FCH170N60		器件	封装	卷尺寸		带宽		数量	
		FCH170N60	TO-247	-	-			30	
电气特性	ET <sub>C</sub> = 25°C	除非另有说明。		· ·			L.		
符号		参数		测试条件		最小值	典型值	最大值	单位
关断特性	<b>I</b>								
	漏极一源极击穿电压		I <sub>D</sub> = 10	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$ $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 150^{\circ}\text{C}$		600	-	-	V
BV <sub>DSS</sub>						650	-	-	V
ΔΒV <sub>DSS</sub> / ΔΤ <sub>J</sub>	击穿电压温度系数			I <sub>D</sub> = 10 mA, 参考 25°C 数值		-	0.67	-	V/°C
	<b>声</b> 加加上		V <sub>DS</sub> =	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V		-	-	1	
IDSS	零栅极电压漏极电流		$V_{DS} = $	$V_{DS} = 480 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$			1.2	1.2 -	μA
I <sub>GSS</sub>	栅极 - 体	漏电流	V <sub>GS</sub> =	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		-	-	±100	nA
导通特性									
V <sub>GS(th)</sub>	栅极阈值	直电压	V <sub>GS</sub> =	V <sub>DS</sub> , I <sub>D</sub> = 250 μA		2.5	-	3.5	V
R <sub>DS(on)</sub>	漏极至源	原极静态导通电阻	V <sub>GS</sub> =	10 V, I <sub>D</sub> = 11 A		-	150	170	mΩ
9 <sub>FS</sub>	正向跨导	}-	V <sub>DS</sub> =	20 V, I <sub>D</sub> = 11 A		-	17	-	S
动态特性									
C <sub>iss</sub>	输入电容	2				-	2150	2860	pF
C <sub>oss</sub>	输出电容			V <sub>DS</sub> = 380 V, V <sub>GS</sub> = 0 V f = 1 MHz V <sub>DS</sub> = 0 V 至 480 V, V <sub>GS</sub> = 0 V		-	60	80	pF
C <sub>rss</sub>	反向传输	间电容	I = I IV			-	2.65	-	pF
C <sub>oss (eff.)</sub>	有效输出	电容	V <sub>DS</sub> =			-	190	-	pF
Q <sub>g(tot)</sub>	10 V 电反	玉的栅极电荷总量	V <sub>DS</sub> =	V <sub>DS</sub> = 380 V, I <sub>D</sub> = 11 A, V <sub>GS</sub> = 10 V (注4)		-	42	55	nC
Q <sub>gs</sub>	栅极 - 源	极栅极电荷				-	9	-	nC
Q <sub>gd</sub>	栅极 - 漏	极"米勒"电荷				-	11	-	nC
ESR	等效串联	电阻	f = 1 N	IHz		-	0.95	-	Ω
开关特性									
t <sub>d(on)</sub>	导通延迟	时间		$V_{DD}$ = 380 V, I <sub>D</sub> = 11 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 4.7 Ω (注 4)		-	21	50	ns
t <sub>r</sub>	导通上升					-	12	35	ns
t <sub>d(off)</sub>	关断延迟		V <sub>GS</sub> =			-	55	120	ns
t <sub>f</sub>	关断下降					-	3.8	18	ns
扁极 - 渡城	及二极管特	itt							
na 10 <b>x</b> - 405-10 I <sub>S</sub>		——102 自 17 III / 漏极 - 源极二极管最大正向连续电流			-	-	22	A	
I <sub>SM</sub>	漏极 - 源极二极管最大正向脉冲电流					-	-	66	Α
V <sub>SD</sub>		极二极管正向电压		V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 11 A		-	-	1.2	V
t <sub>rr</sub>	反向恢复		$V_{GS} = 0 V, I_{SD} = 11 A$		-	346	-	ns	
Q <sub>rr</sub>	反向恢复			$dI_{F}/dt = 100 \text{ A}/\mu \text{s}$		-	6.2	-	μC

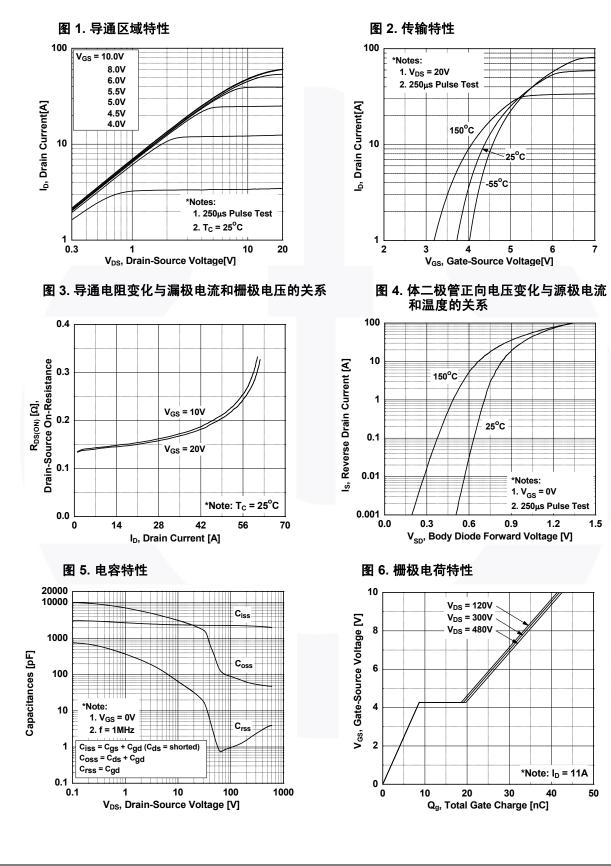
1. 重复额定值: 脉冲宽度受限于最大结温

2. I<sub>AS</sub> = 5 A, R<sub>G</sub> = 25  $\Omega$ , 开始于 T<sub>J</sub> = 25°C 3. I<sub>SD</sub>  $\leq$  11 A, di/dt  $\leq$  200 A/µs, V<sub>DD</sub>  $\leq$  380 V, 开始于 T<sub>J</sub> = 25°C

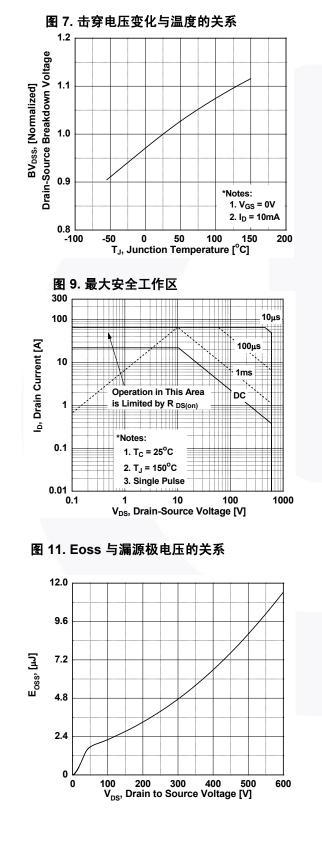
4. 本质上独立于操作温度的典型特性

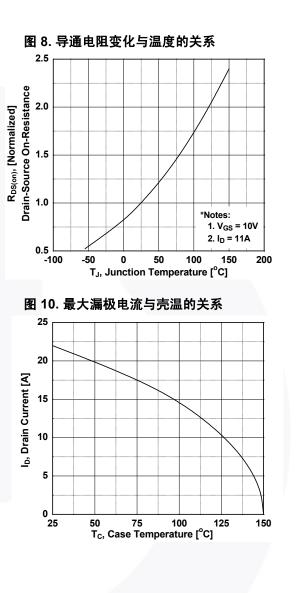
# FCH170N60 — N 沟道 SuperFET<sup>®</sup> II MOSFET

### 典型性能特征



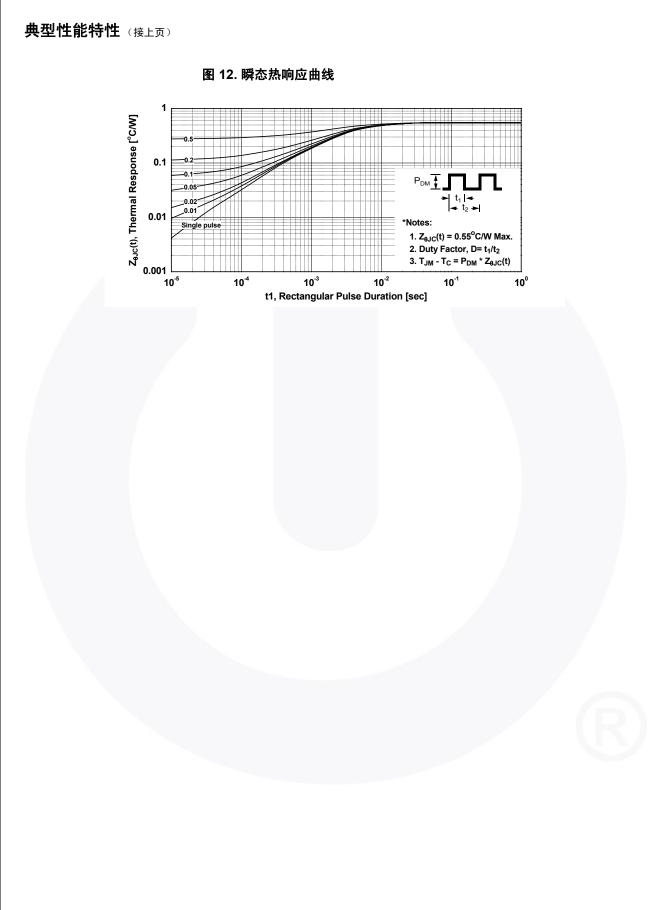
### 典型性能特性 (接上页)



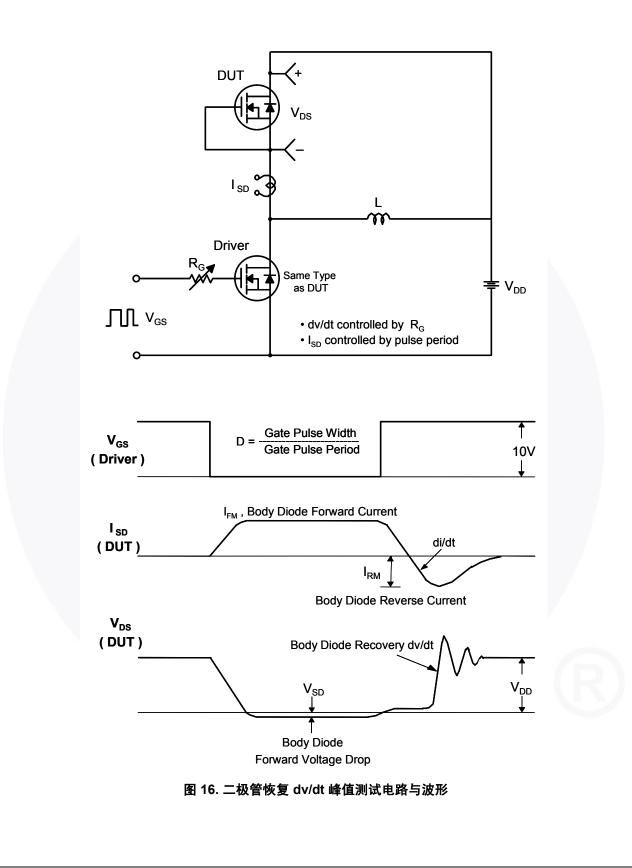


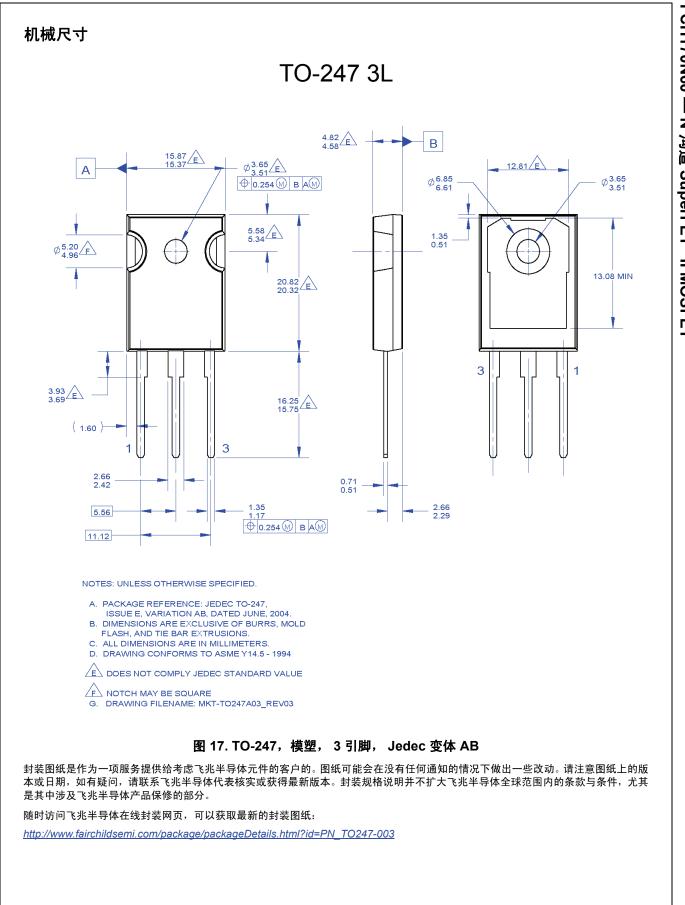
FCH170N60 — N 沟道 SuperFET<sup>®</sup> II MOSFET

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 $V_{GS}$ ≲ק  $\mathsf{Q}_\mathsf{g}$ FV<sub>DS</sub>  $\mathsf{Q}_{\mathsf{gd}}$  $\mathsf{Q}_{\mathsf{gs}}$ 5 DUT I<sub>G</sub> = 常量 Charge 图 13. 栅极电荷测试电路与波形 R VDS V<sub>DS</sub> 90% ο V<sub>DD</sub> V<sub>GS</sub>  $R_{G}$ 10% V<sub>GS</sub> DUT V<sub>GS</sub> ∏ a 图 14. 阻性开关测试电路与波形 L  $E_{AS} = \frac{1}{2} L I_{AS}^2$ VDS  $\mathsf{BV}_{\mathsf{DSS}}$ ID a I<sub>AS</sub>  $\mathsf{R}_{\mathsf{G}}$ ₽ V<sub>DD</sub> I<sub>D</sub> (t) 10V V<sub>GS</sub> ]  $V_{DS}(t)$  $V_{\text{DD}}$ DUT Time t<sub>p</sub> 图 15. 非箝位电感开关测试电路与波形







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